

Cascadable Amplifier
10 to 1000 MHz

A18-1 / SMA18-1

V3

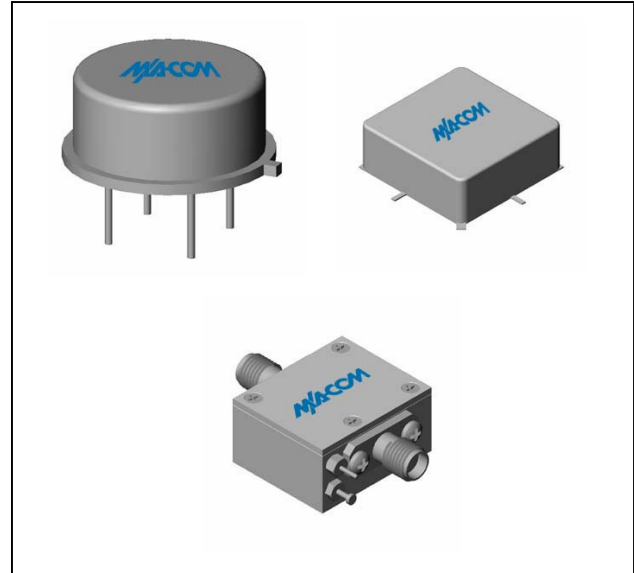
Features

- HIGH DYNAMIC RANGE
- HIGH OUTPUT POWER: +16 dBm (TYP.)
- HIGH THIRD ORDER I.P.: +30 dBm (TYP.)
- LOW NOISE: 3.8 dB (TYP.)

Description

The A18-1 RF amplifier is a discrete hybrid design, which uses thin film manufacturing processes for accurate performance and high reliability. This single stage GaAs FET feedback amplifier design displays impressive performance characteristics over a broadband frequency range. An RF choke is used for DC power supply decoupling. Both TO-8 and Surface Mount packages are hermetically sealed, and MIL-STD-883 environmental screening is available.

Product Image



Ordering Information

| Part Number | Package |
|-------------|-------------------|
| A18-1 | TO-8 |
| SMA18-1 | Surface Mount |
| CA18-1 | SMA Connectorized |

Electrical Specifications: $Z_0 = 50\Omega$, $V_{CC} = +15 V_{DC}$

| Parameter | Units | Typical | Guaranteed | |
|---------------------------------|-------|---------------|---------------|----------------|
| | | 25°C | 0° to 50°C | -54° to +85°C* |
| Frequency | MHz | 5-1100 | 10-1000 | 10-1000 |
| Small Signal Gain (min) | dB | 14.7 | 14.0 | 13.5 |
| Gain Flatness (max) | dB | ±0.3 | ±0.5 | ±1.0 |
| Reverse Isolation | dB | 17 | | |
| Noise Figure (max) | dB | 3.8 | 5.0 | 5.5 |
| Power Output @ 1 dB comp. (min) | dBm | 16.0 | 15.0 | 14.5 |
| IP3 | dBm | +30 | | |
| IP2 | dBm | +42 | | |
| Second Order Harmonic IP | dBm | +45 | | |
| VSWR Input / Output (max) | | 1.5:1 / 1.5:1 | 1.8:1 / 1.8:1 | 2.0:1 / 2.0:1 |
| DC Current @ 15 Volts (max) | mA | 44 | 46 | 48 |

Absolute Maximum Ratings

| Parameter | Absolute Maximum |
|--|------------------|
| Storage Temperature | -62°C to +125°C |
| Case Temperature | +125°C |
| DC Voltage | +17 V |
| Continuous Input Power | +13 dBm |
| Short Term Input power (1 minute max.) | 50 mW |
| Peak Power (3 μsec max.) | 0.5 W |
| "S" Series Burn-In Temperature (case) | +125°C |

Thermal Data: $V_{CC} = +15 V_{DC}$

| Parameter | Rating |
|---|---------|
| Thermal Resistance θ_{jc} | 145°C/W |
| Transistor Power Dissipation P_d | 0.4 W |
| Junction Temperature Rise Above Case T_{jc} | +58°C |

* Over temperature performance limits for part number CA18-1, guaranteed from 0°C to +50°C only.

